

#### **P-Channel MOSFET**

### **General Description**

The WSD90P06DN56 is the highest performance trench P-Channel MOSFETs with extreme high cell density, which provide excellent  $R_{DS(ON)}$  and gate charge for most of the synchronous buck converter applications.

The WSD90P06DN56 meet the RoHS and Green Product requirement, 100%  $E_{AS}$  guaranteed with full function reliability approved.

#### **Product Summery**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	Ι <sub>D</sub>
-60V	10mΩ	-90A

#### Applications

- Power Management
- Load Switch

#### **DFN5X6-8L Pin Configuration**



### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% E<sub>AS</sub> Guaranteed
- Green Device Available

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-60	v
V <sub>GS</sub>	Gate-Source Voltage	±20	
I <sub>D</sub> @T <sub>C</sub> =25°C	I <sub>D</sub> @T <sub>C</sub> =25°C Continuous Drain Current, V <sub>GS</sub> @ -10V		
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ -10V	-40	A
I <sub>DM</sub>	Pulsed Drain Current	-190	
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation	96	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	

#### **Absolute Maximum Ratings**

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Units
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient		62	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case		1.3	C/VV



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### Electrical Characteristics (T<sub>J</sub>=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250µA	-60			V
P	Statia Drain Source On Registeres	V <sub>GS</sub> =-10V , I <sub>D</sub> =-18A		10	14	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-12A		13	18	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_{D}=-250\mu A$	-1.1	-1.8	-2.5	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-48V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			-1.0	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	$V_{GS}$ =±20V , $V_{DS}$ =0V			±100	nA
Qg	Total Gate Charge			89		
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-30V,V <sub>GS</sub> =-10V,I <sub>D</sub> =-17A		12		nC
Q <sub>gd</sub>	Gate-Drain Charge			32		
T <sub>d(on)</sub>	Turn-On Delay Time			15		
Tr	Rise Time	$V_{DD}$ =-30V , R <sub>L</sub> =30 $\Omega$ , I <sub>D</sub> =-1A ,		13		
T <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GEN</sub> =-10V , R <sub>G</sub> =6Ω		110		ns
T <sub>f</sub>	Fall Time			60		
C <sub>iss</sub>	Input Capacitance			4066		
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-30V , V <sub>GS</sub> =0V , f=1.0MHz		501		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			291		

#### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
ا <sub>S</sub>	Continuous Source Current	T <sub>C</sub> =25°C			-40	А
V <sub>SD</sub>	Diode Forward Voltage	$V_{GS}$ =0V , $I_{S}$ =-1A , $T_{J}$ =25°C			-1.2	V

Note:

1. The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A$ =25°C. The value in any given application depends on the user's specific board design.

2. Repetitive rating, pulse width limited by junction temperature.

3. The current rating is based on the t≤10s junction to ambient thermal resistance rating.



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## **Typical Characteristics**





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## **Typical Characteristics (Cont.)**







Fig.10 Switching Time Waveform



Fig.11 Unclamped Inductive Waveform



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## **Packaging information**





	MILLIMETERS				
SYMBOLS -	MIN.	NOM.	MAX.		
A	0.90	1.05	1.20		
b	0.35	0.40	0.50		
С	0.20	0.25	0.35		
D	4.90	5.05	5.20		
D1	3.72	3.82	3.92		
E	6.00	6.15	6.30		
E1	5.60	5.75	5.90		
E2	3.47	3.57	3.67		
е		1.27 BSC.			
Н	0.48	0.58	0.68		
К	1.17	1.27	1.37		
L	0.64	0.74	0.84		
L1/L2		0.20 REF.			
θ	8°	10° 12°			
М		0.08 REF.			
N	0	- 0.15			
0		0.25 REF.			
Р		1.28 REF.			



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